BFP760

High Gain and High Linearity Low Noise Amplifier for 2.4 GHz WLAN

Application Note AN310

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Previous Revision:

Page	Subjects (major changes since last revision)

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Last Trademarks Update 2011-11-11

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1 About Wireless Fidelity (Wi-Fi®) / Wireless LAN (WLAN)

Wireless Fidelity (Wi-Fi®) or well-known as wireless LAN (WLAN) plays a major role in today's communications by enabling constant connection in the 2.4 GHz and broadband Internet access for users with laptops or devices equipped with wireless network interface while roaming within the range of fixed access points (AP) or a public hotspot. Different applications like home entertainment with wireless high-quality multimedia signal transmission, home networking notebooks, mass data storages and printers implement 2.4 GHz into their system for wireless connectivity. For this kind of high-speed high data rate wireless communication standards it is essential to ensure the quality of the link path. Major performance criteria of these equipments have to be fulfilled: sensitivity, strong signal capability and interference immunity. Below a general application diagram of a WLAN system is shown.

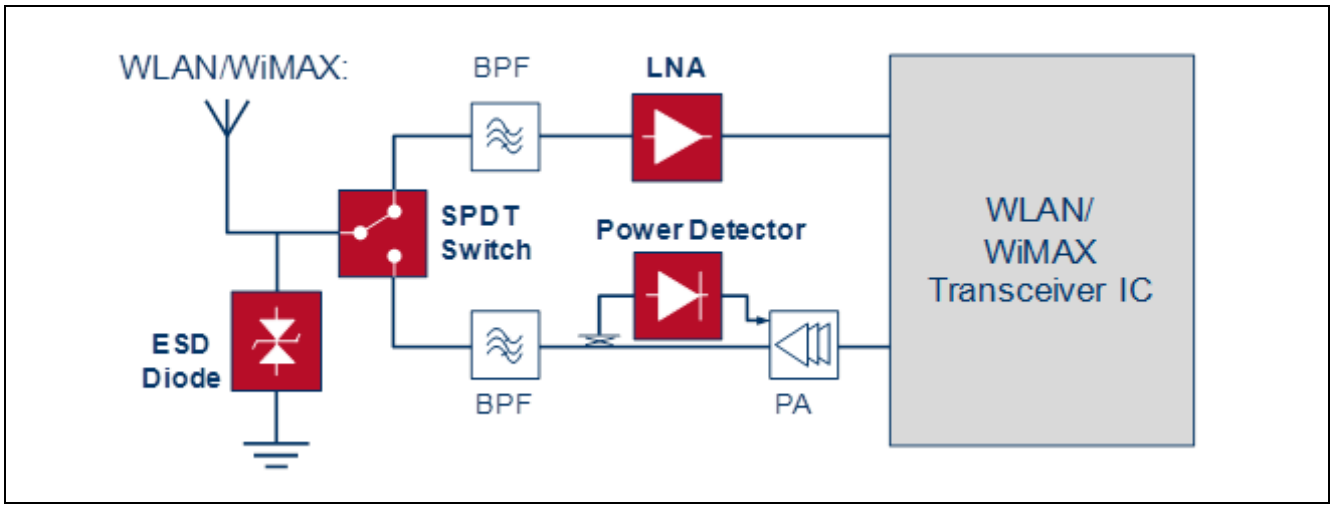

Figure 1 2.4 GHz Wi-Fi® Wireless LAN (WLAN, IEEE802.11b/g/n/a/c/ac) Front-End

In order to increase the system sensitivity, an excellent low noise amplifier (LNA) in front of the receiver is mandatory, especially in an environment with very weak signal strength and because of the insertion loss of the single-pole-double-throw (SPDT) switch and the Bandpass Filter (BPF) or diplexer. The typical allowed receiver chain Noise Figure (NF) of approx. 2 dB can only be achieved by using a high-gain low noise amplifier (LNA).

In addition, strong signal environment can exist when the equipment is next to a transmitter. In that case, the LNA must be linear enough, i.e. have high 1dB compression point. This avoids saturation, degradation of the gain and increased noise figure.

This application note is focusing on the LNA block, but Infineon does also support with RF-switches, TVS-diodes for ESD protection and RF Schottky diodes for power detection.

2 BFP760 Overview

2.1 Features

- Very low noise amplifier based on Infineon´s reliable, high volume SiGe:C technology.
- High linearity *OIP*3 = 27 dBm @ 5.5 GHz, 3 V, 30 mA.
- High transition frequency *f*T = 45 GHz @ 1 GHz, 3 V, 35mA.
- *NF*min = 0.95 dB @ 5.5 GHz, 3 V, 10 mA,
- Transducer gain |*S*21|2 = 16 dB @ 3.5 GHz, 3 V, 10 mA.
- Low power consumption, ideal for mobile applications.
- Easy to use Pb-free (RoHS compliant) and halogen-free standard package with visible leads
- Qualification report according to AEC-Q101 available.

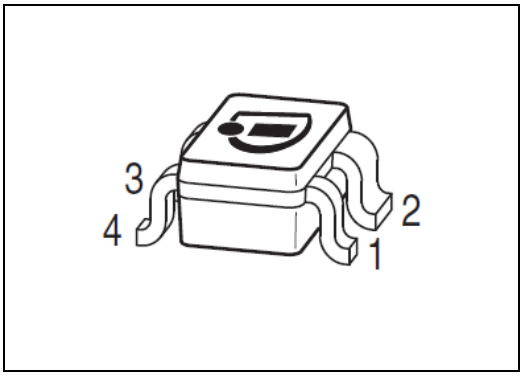

Figure 2 BFP760 in SOT343

2.2 Key Applications of BFP760

- As Low Noise Amplifier (LNA) in
  - Mobile and fixed connectivity applications: WLAN 802.11a/b/c/g/n, WiMAX 2.5/3.5 GHz, Bluetooth
  - Satellite communication systems: Navigation systems (GPS, Glonass), satellite radio (SDARs, DAB) and C-band LNB
  - Multimedia applications such as mobile/portable TV, CATV, FM Radio
  - UMTS/LTE mobile phone applications
  - ISM applications like RKE, AMR and Zigbee, as well as for emerging wireless applications

- As discrete active mixer, buffer amplifier in VCOs

2.3 Description

The BFP760 is a linear low noise wideband NPN bipolar RF transistor. The device is based on Infineon's reliable high volume silicon germanium carbon (SiGe:C) heterojunction bipolar technology. The collector design supports voltages up to V_{CEO} = 4.0 V and currents up to I_C = 70 mA. With its high linearity at currents as low as 10 mA the device supports energy efficient designs. The typical transit frequency is approximately 45 GHz. The device is housed in an easy to use plastic SOT-343 package with visible leads.

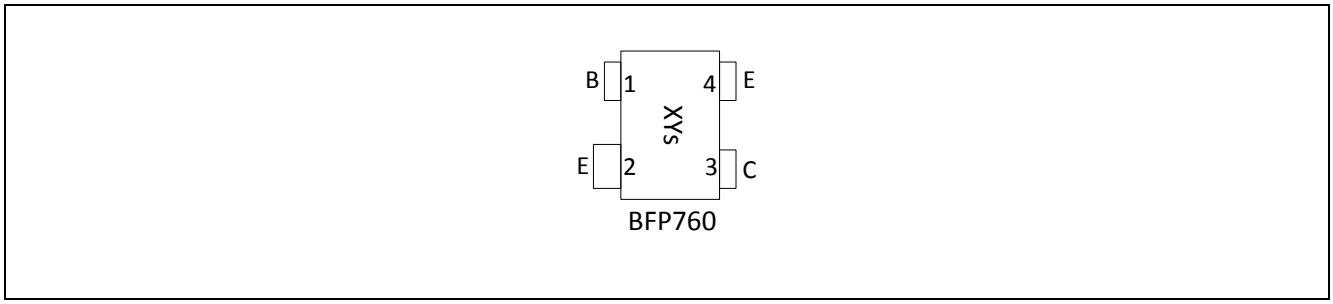

Figure 3 Package and pin definations of BFP760

Table 1 Pin Assignment of BFP760

Pin No.	Symbol	Function
1	B	Transitor base
2	E	Transitor emitter
3	C	Transitor collector
4	E	Transitor emitter

3 Application Circuit and Performance Overview

Device: BFP760
Application: High Gain and High Linearity Low Noise Amplifier for 2.4 GHz WLAN
PCB Marking: M130125 V1.4e

3.1 Summary of Measurement Results

Table 2 Electrical Characteristics (at room temperature)

Parameter	Symbol	Value	Unit	Comment/Test Condition
Frequency Range	Freq	2.4-2.5	GHz	
DC Voltage	Vcc	3.0	V	
DC Current	Icc	14.5	mA	
Gain (on mode)	G_{on}	16.7	dB	
Gain (off mode)	G_{off}	-16.3	dB	
Noise Figure	NF	0.92	dB	SMA and PCB losses (~0.06 dB) are subtracted
Input Return Loss	RLin	13	dB	
Output Return Loss	RLout	13	dB	
Reverse Isolation	IRev	24.2	dB	
Input P1dB (On mode)	$IP1dB_{on}$	-9.7	dBm	
Input P1dB (Off mode)	$IP1dB_{off}$	>10		
Output P1dB(On mode)	$OP1dB_{on}$	7	dBm	
Input IP3	IIP3	-0.2	dBm	Power @ Input: -30 dBm f_1= 2440 MHz, f_2= 2441 MHz
Output IP3	OIP3	16.5	dBm	Power @ Input: -30 dBm f_1= 2440 MHz, f_2= 2441 MHz
Stability	k	≥ 1.0	--	Stability measured from 10MHz to 15GHz

3.2 BFP760 as Low Noise Amplifier for 2.4 GHz WLAN

This application note presents the high gain low noise amplifier using BFP760 for 2.4 GHz WLAN applications.

The circuit requires only nine 0402 passive components. It has in band gain of 16.7dB. The circuit achieves an input and output return loss more than 12 dB. The noise figure is about 0.92 dB (SMA and PCB losses are subtracted) for the whole frequency band. Furthermore, the circuit is unconditionally stable till 15 GHz. At 2440 MHz, using two tones spacing of 1 MHz, the output third order intercept point OIP3 reaches 16.5 dBm. Input 1dB compression point IP1dB of -9.7 dBm. The off mode gain is about -16 dB. The input P1dB compression in the off-mode for the whole frequency range is more than 10 dBm.

3.3 Schematics and Bill-of-Materials

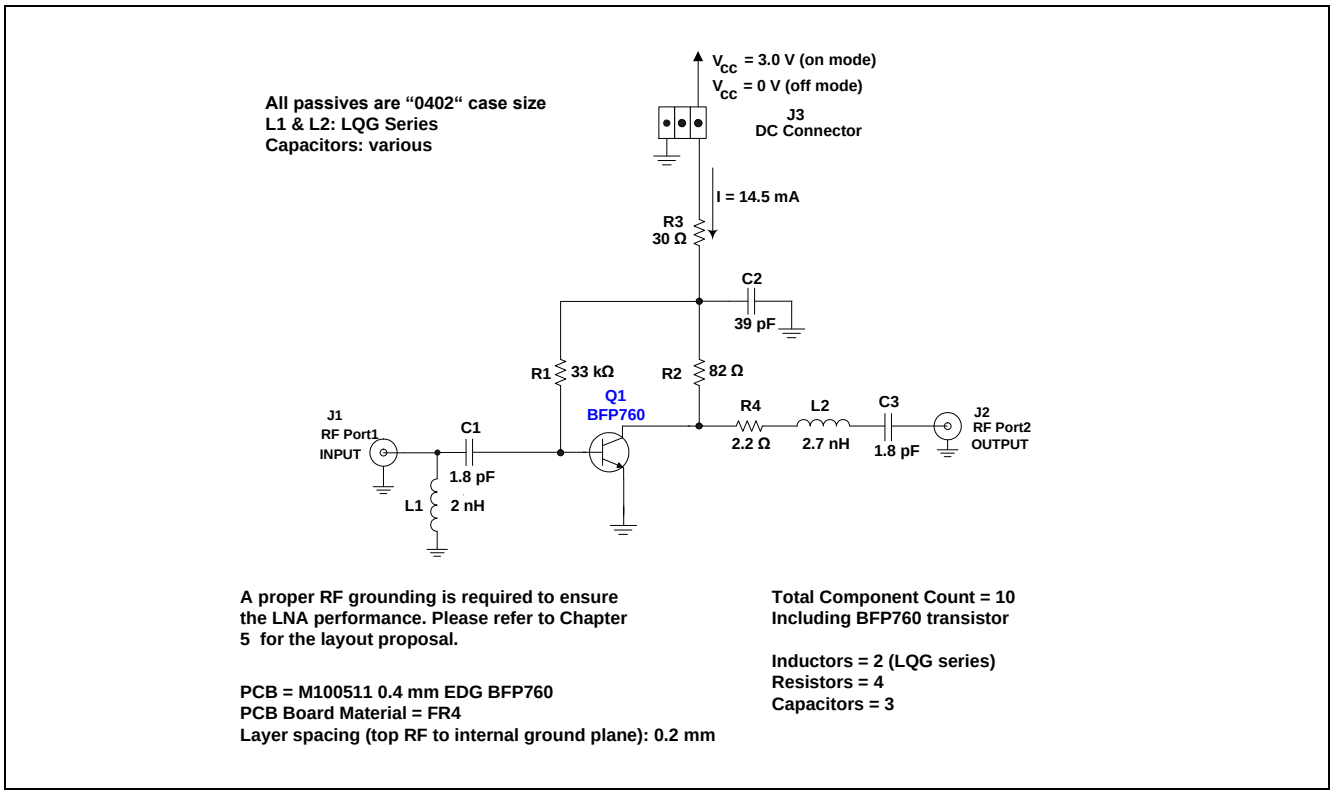

Figure 4 Schematics of the BFP760 Application Circuit

Table 3 Bill-of-Materials

Symbol	Value	Unit	Size	Manufacturer	Comment
C1	1.8	pF	0402	Various	Input DC block & input matching
C2	39	pF	0402	Various	RF decoupling / blocking cap
C3	1.8	pF	0402	Various	Output DC block & output matching
L1	2	nH	0402	Murata LQG series	Input matching
L2	2.7	nH	0402	Murata LQG series	Output matching
R1	33	kΩ	0402	Various	DC biasing
R2	82	Ω	0402	Various	Stability improvement
R3	30	Ω	0402	Various	DC biasing (provides DC negative feedback to stabilize DC operating point over temperature variation, transistor h_{FE} variation, etc.)
R4	2.2	Ω	0402	Various	Stability improvement and output matching
R4	18	kΩ	0402	Various	Bypass mode DC biasing
Q1			SOT343	Infineon Technologies	BFP760 SiGe: C Heterojunction Bipolar RF Transistor

4 Measurement Graphs

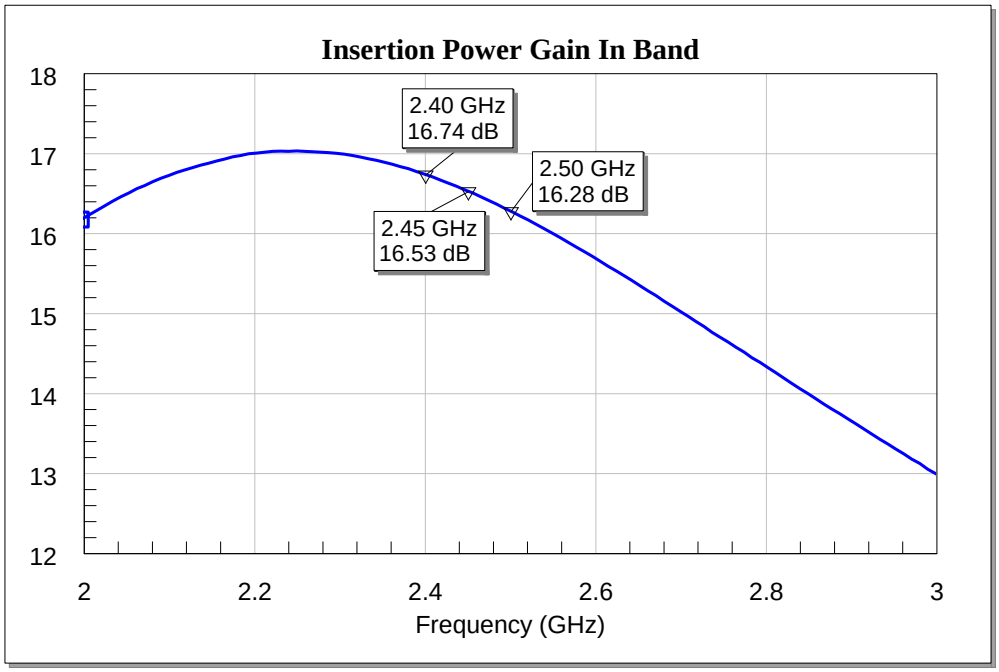

Figure 5 Insertion Power Gain of the 2.4 GHz WLAN LNA with BFP760

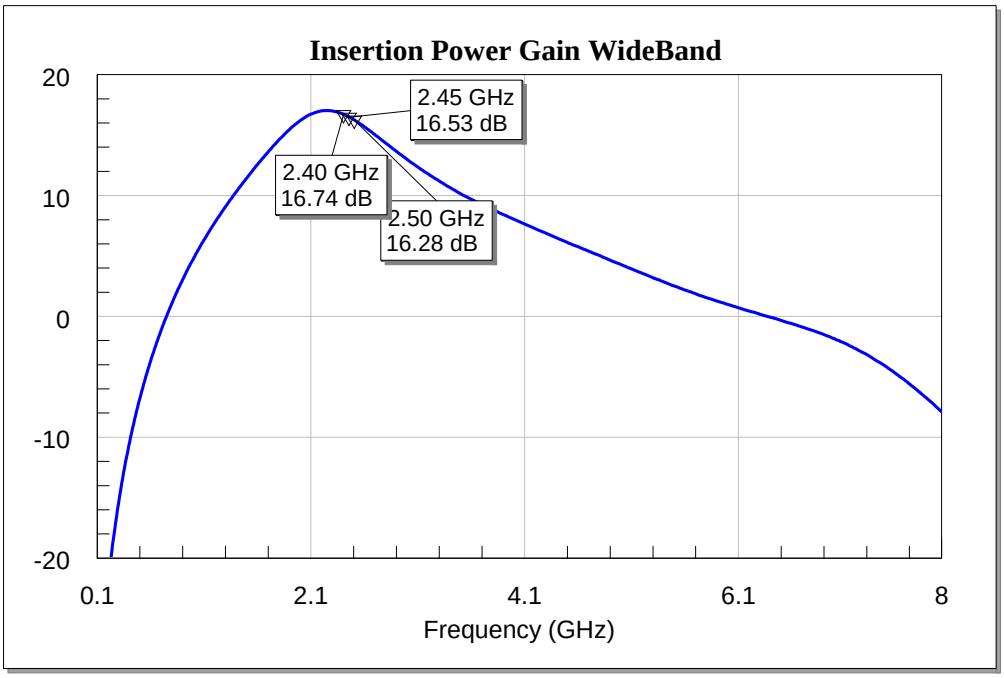

Figure 6 Wideband Insertion Power Gain of the 2.4 GHz WLAN LNA with BFP760

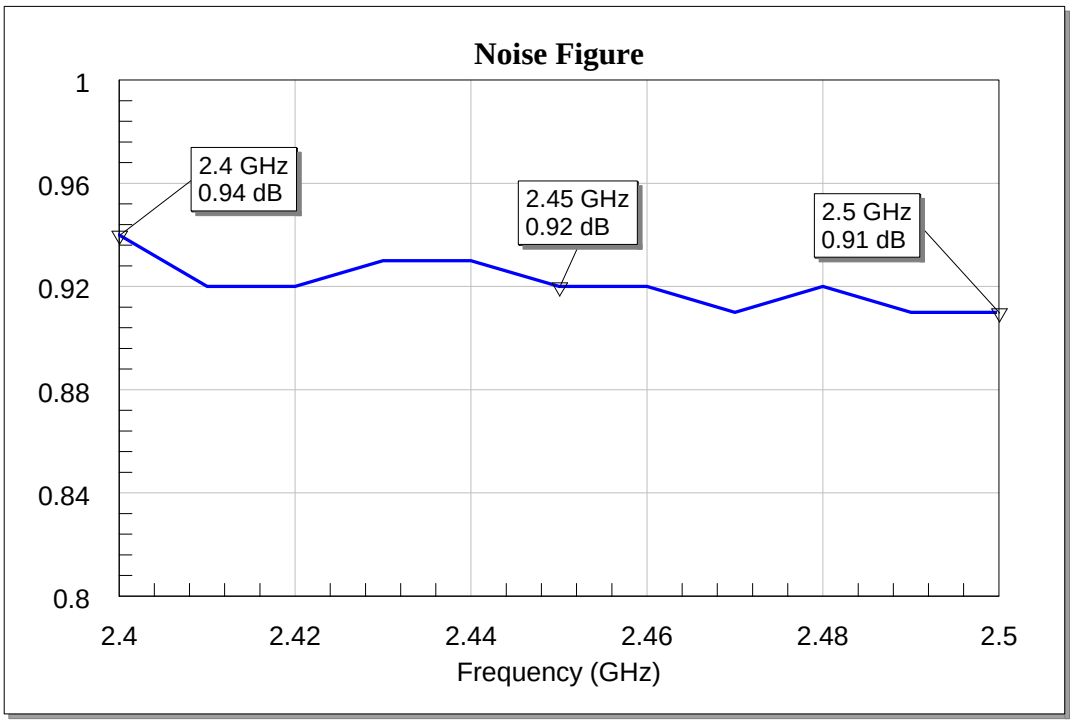

Figure 7 Noise Figure of BFP760 LNA for 2.4 - 2.5 GHz

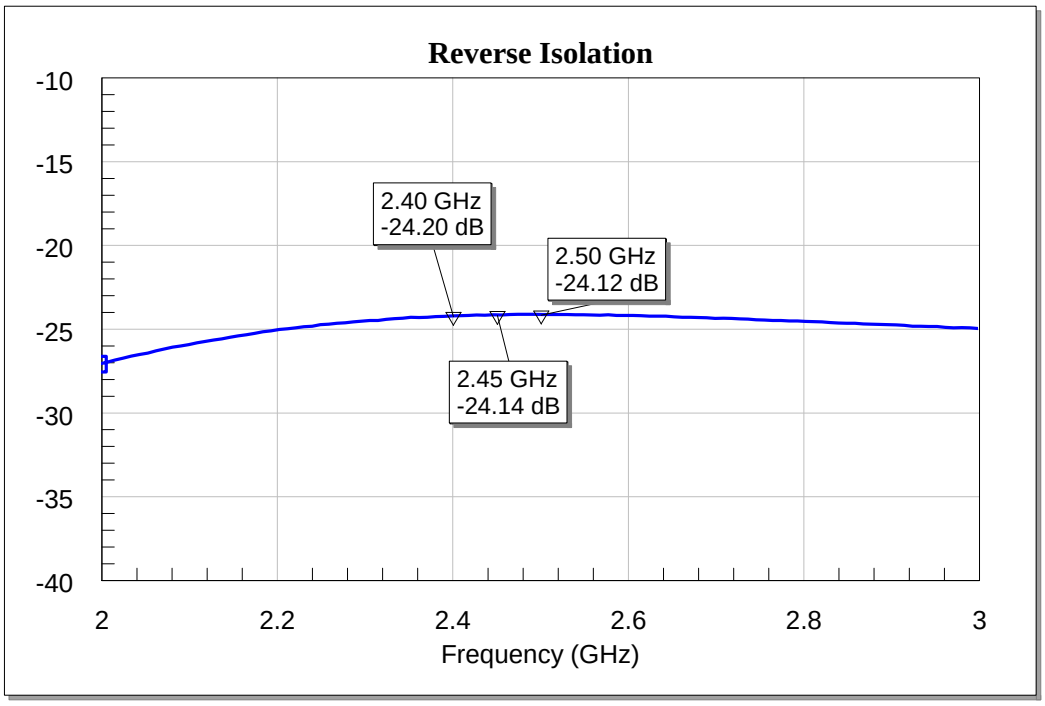

Figure 8 Reverse Isolation of the 2.4 GHz WLAN LNA with BFP760

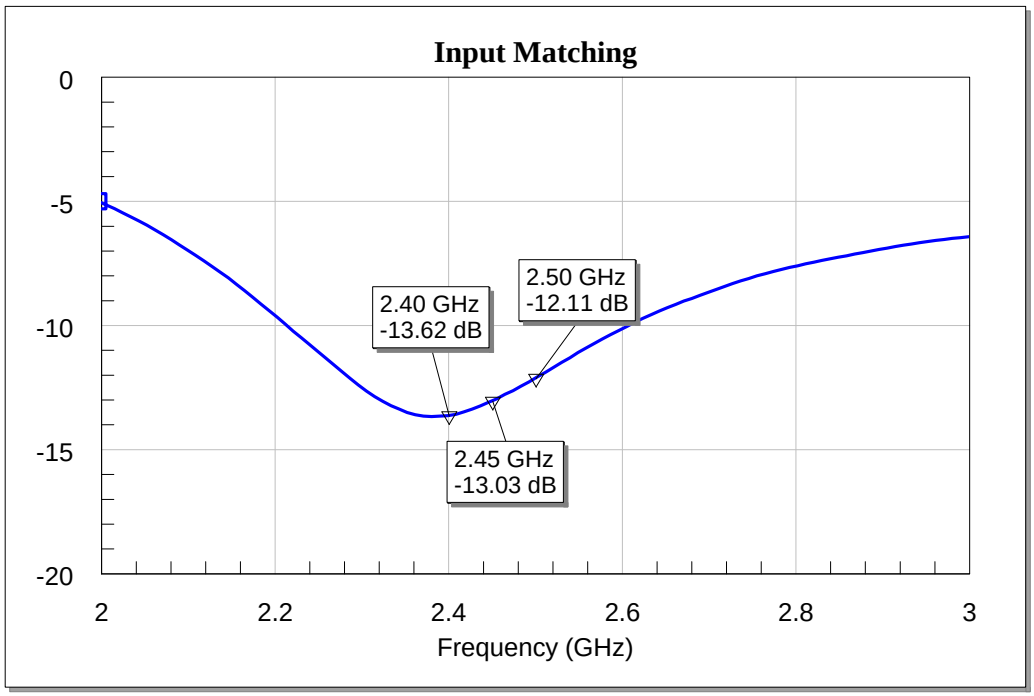

Figure 9 Input Matching of the 2.4 GHz WLAN LNA with BFP760

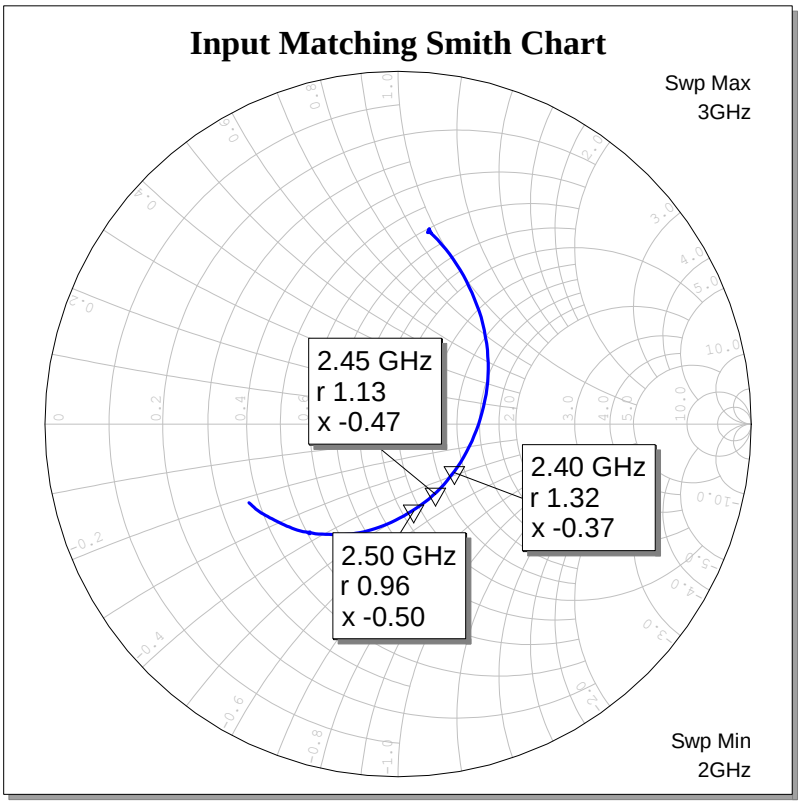

Figure 10 Input Matching of 2.4 GHz WLAN LNA with BFP760 (Smith Chart)

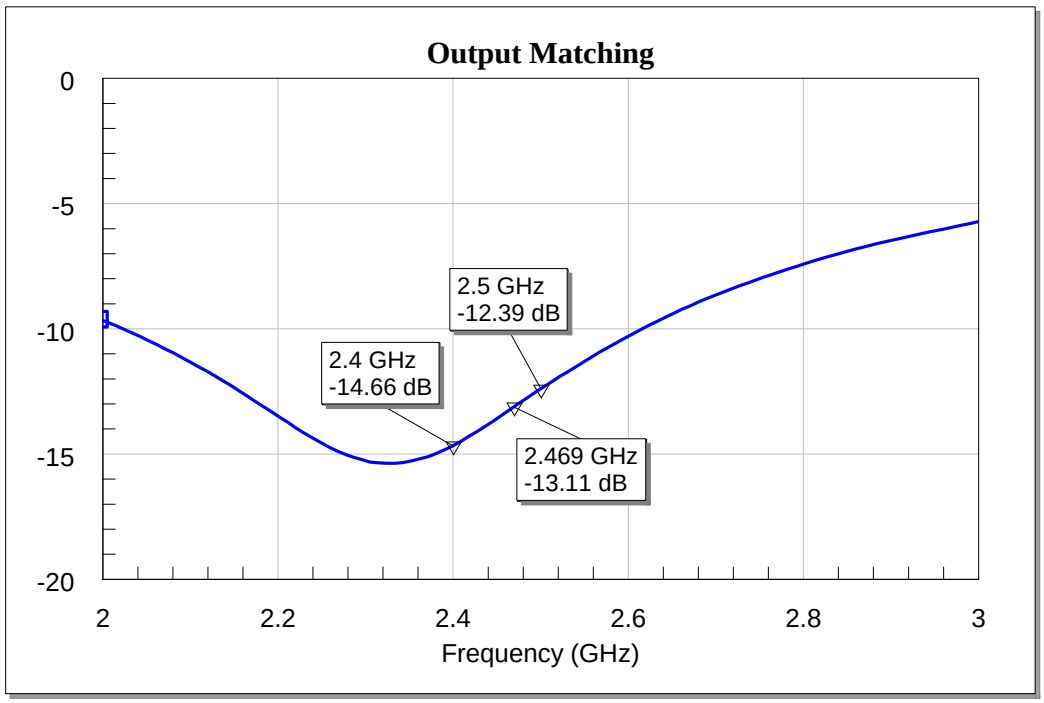

Figure 11 Output Matching of the 2.4 GHz WLAN LNA with BFP760

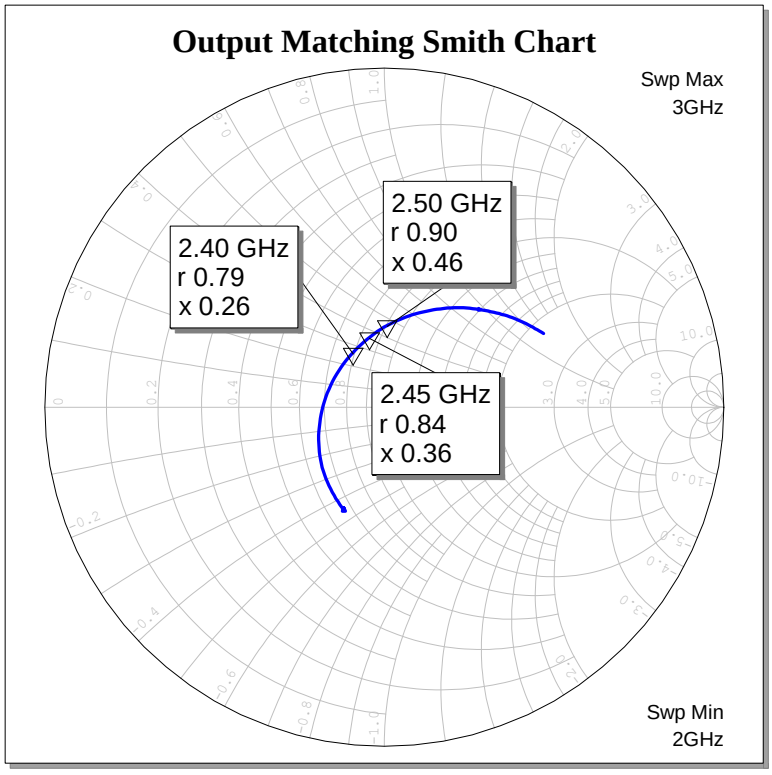

Figure 12 Output Matching of the 2.4 GHz WLAN LNA with BFP760 (Smith Chart)

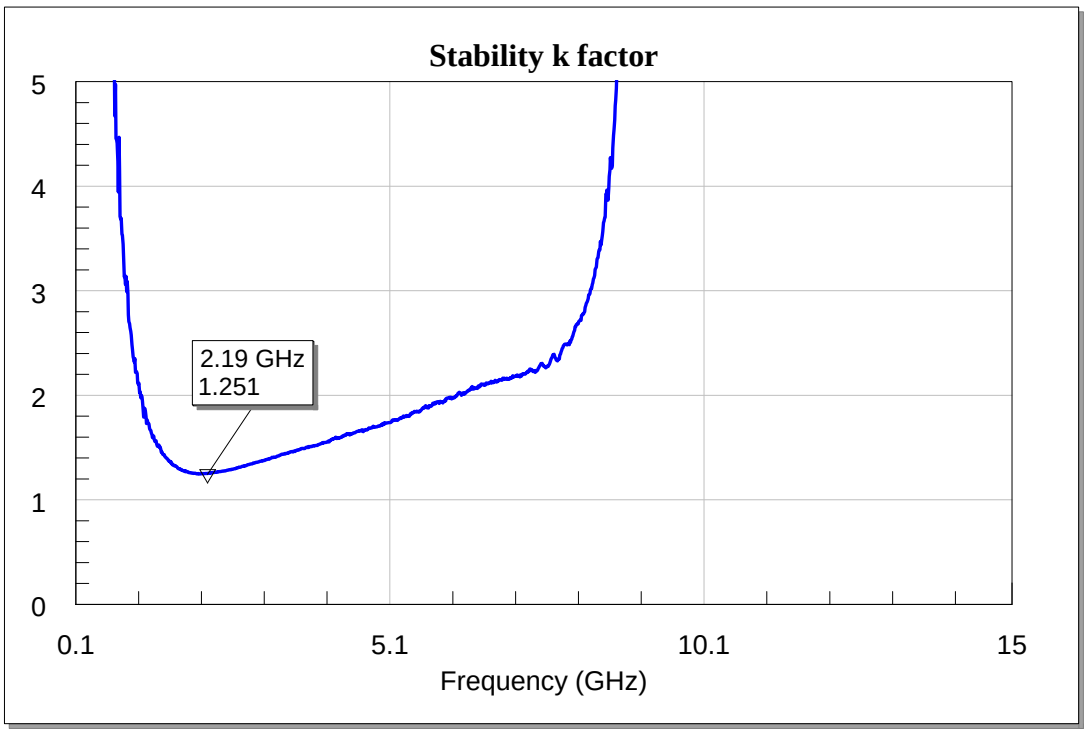

Figure 13 Wideband Stability k Factor of the 2.4 GHz WLAN LNA with BFP760

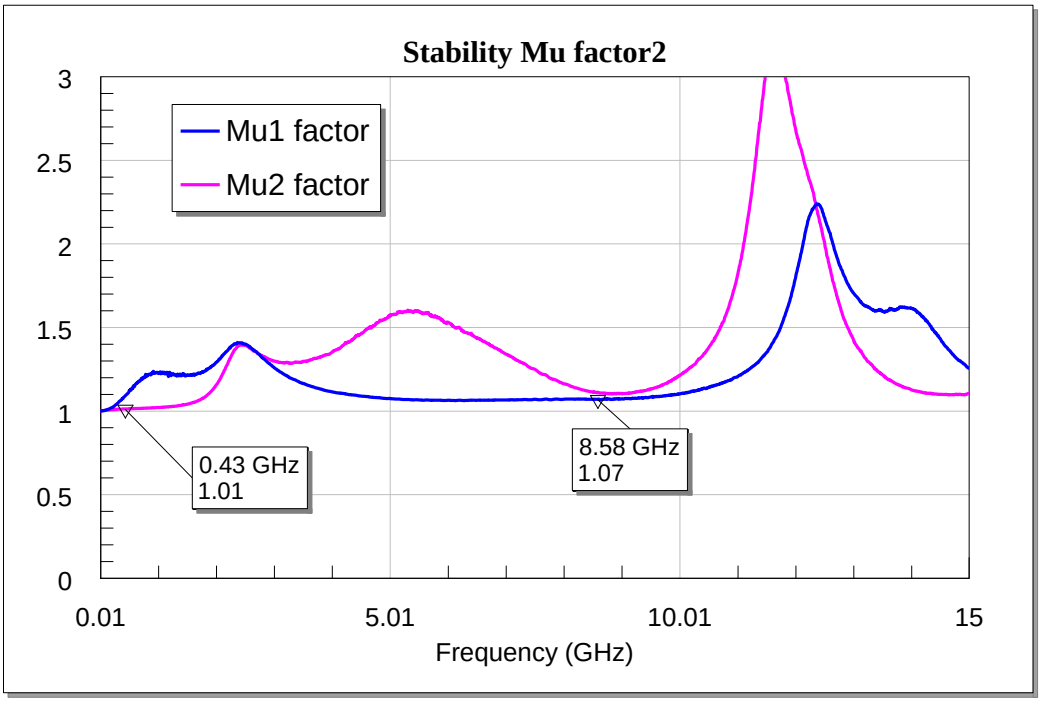

Figure 14 Wideband Stability Mu Factor of the 2.4 GHz WLAN LNA with BFP760

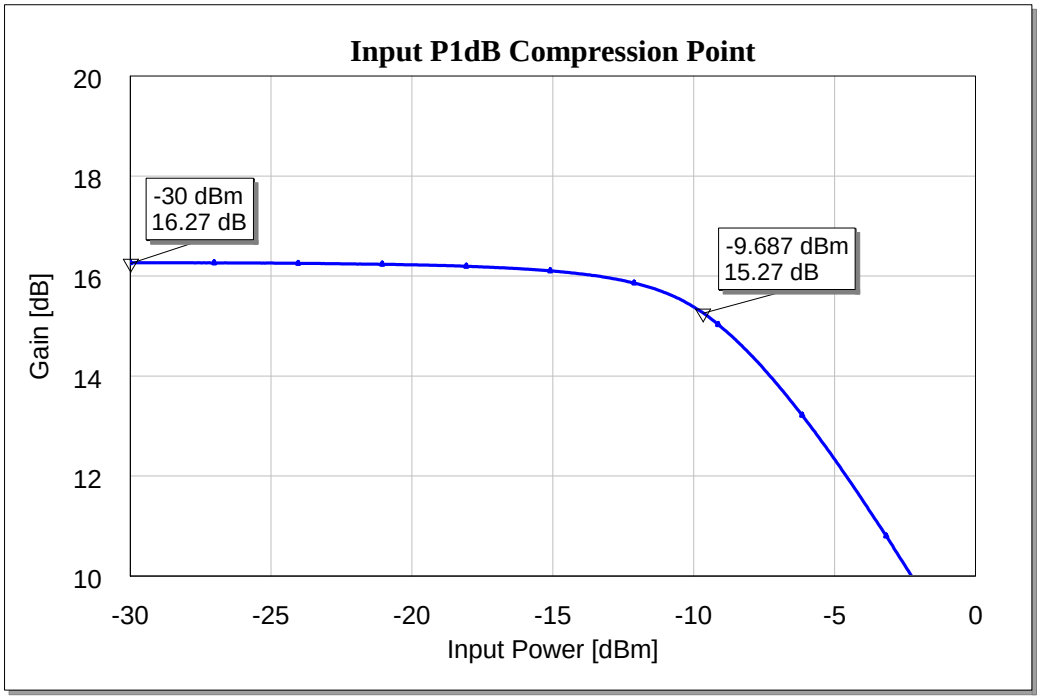

Figure 15 Input 1dB Compression Point of the BFP760 Circuit

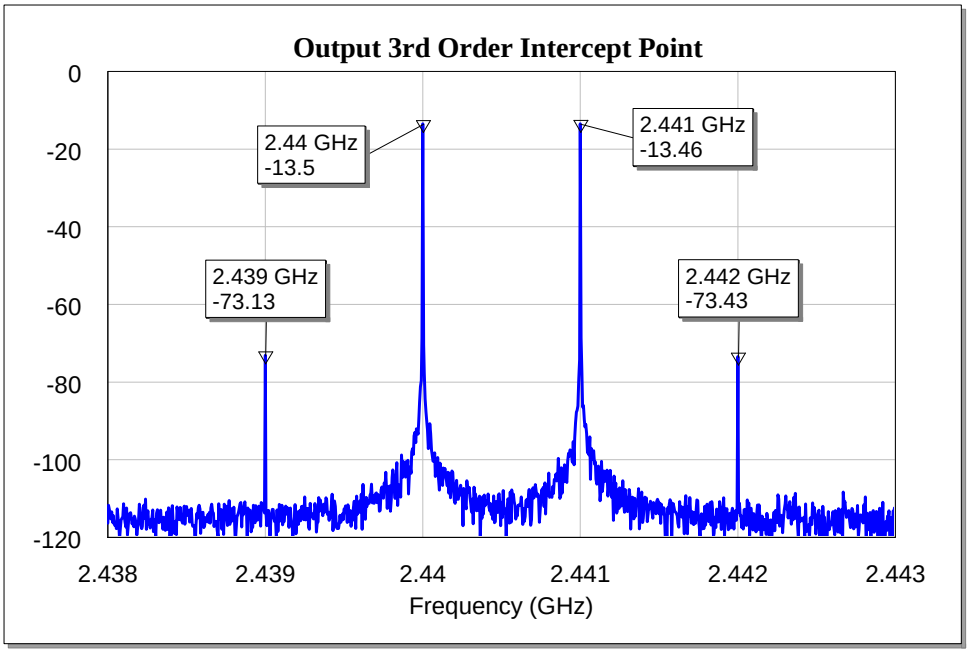

Figure 16 Output 3rd Order Intercept Point of BFP760 at 2440 MHz

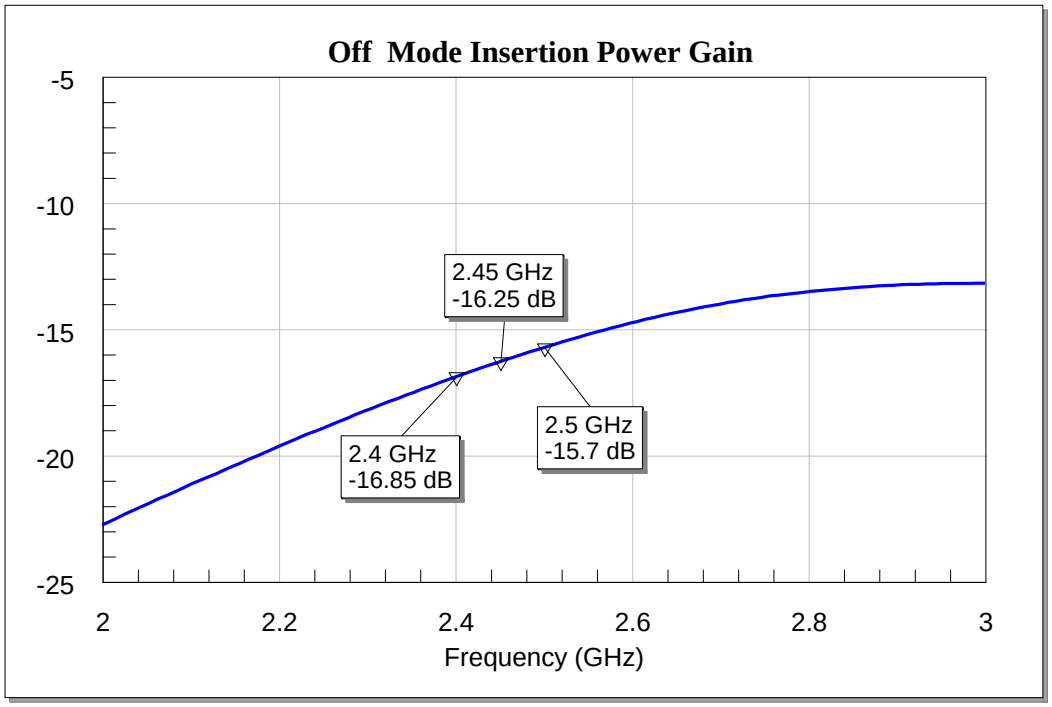

Figure 17 Off mode Insertion Power Gain of the 2.4 GHz WLAN LNA with BFP760

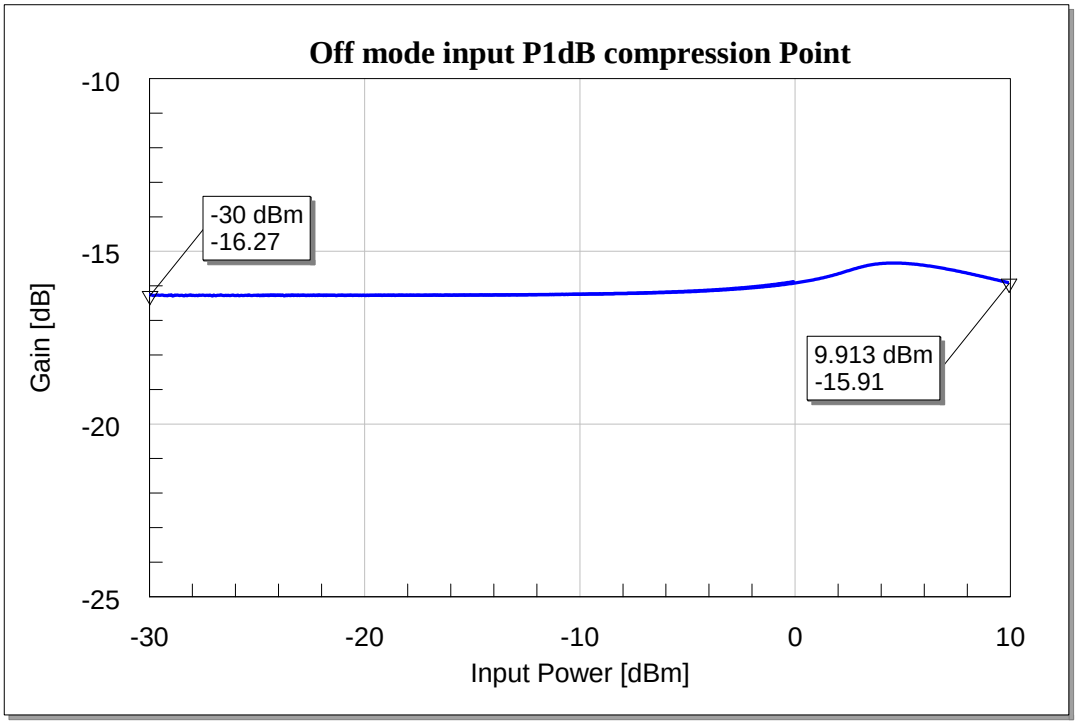

Figure 18 Off mode input 1dB compression point of the 2.4 GHz WLAN LNA with BFP760

5 Evaluation Board and Layout Information

In this application note, the following PCB is used:

PCB Marking: M130125 V1.4e

PCB material: FR4

ε_r of PCB material:4.3 (FR4)

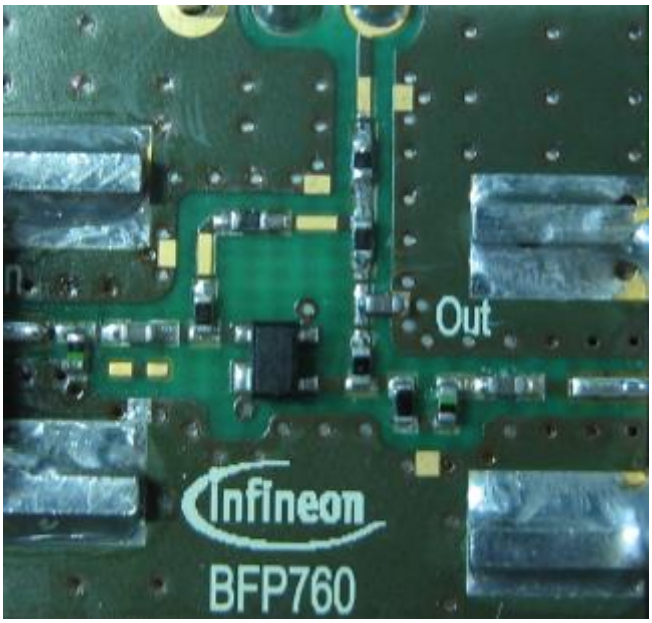

Figure 19 Photo Picture of Evaluation Board (overview) <PCB Marking Myymmdd Rev. x.x>

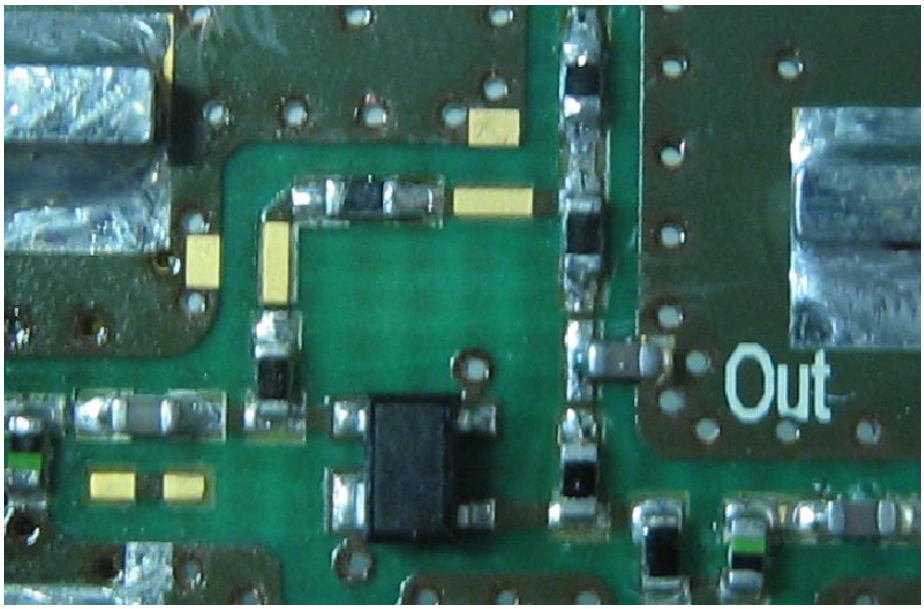

Figure 20 Photo Picture of Evaluation Board (detailed view)

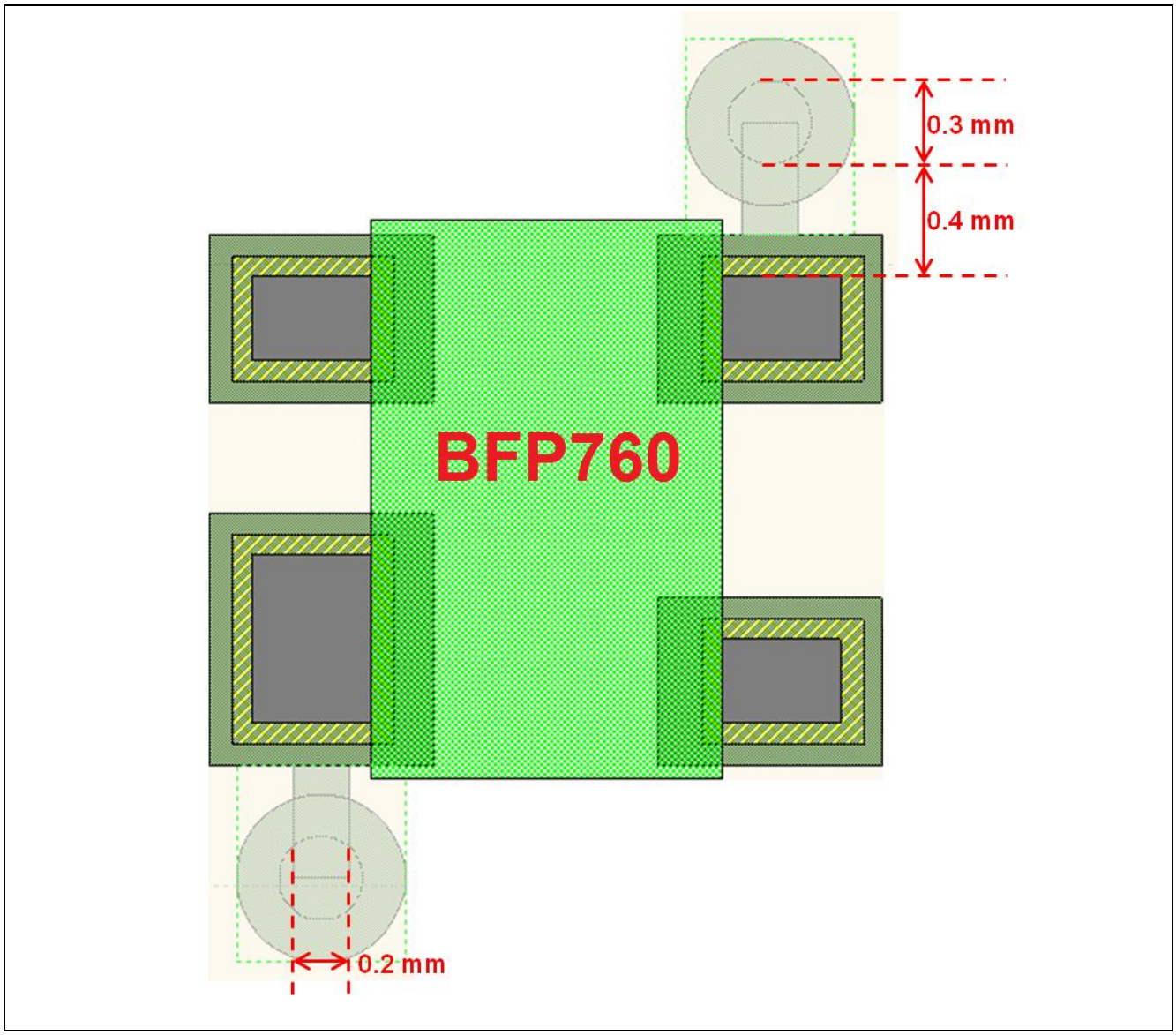

Figure 21 Layout Proposal for RF Grounding of the 2.4 GHz WLAN LNA with BFP760

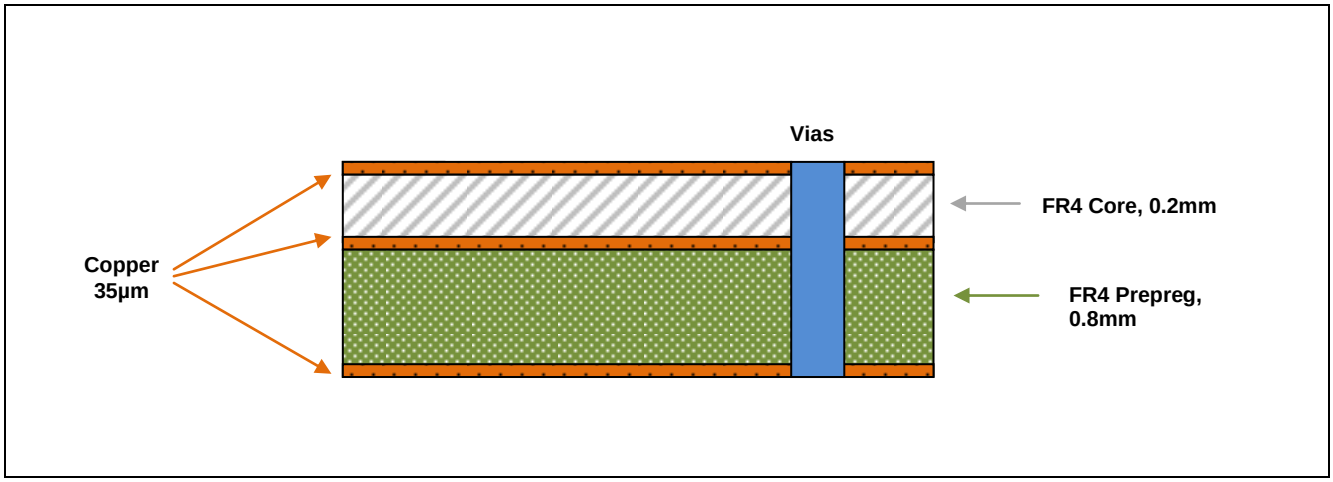

Figure 22 PCB Layer Information

6 Authors

Moakhkhrul Islam, Application Engineer, Technical Marketing RF of Business Unit “RF and Protection Devices”

Dr. Chih-I Lin, Senior Staff Engineer, Technical Marketing RF of Business Unit “RF and Protection Devices”

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